# MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED

# ESD9N12BA-MS

**Product specification** 





#### **Features**

Small Body Outline Dimensions:
0.039" x 0.024"(1.0 mm x 0.60 mm)

Low Body Height: 0.020" (0.50 mm) Max

Stand-off Voltage: 12 V

Low Leakage

Response Time is Typically < 1 ns</li>

 ESD Rating of Class 3 (> 16 kV) per Human Body Model

IEC61000-4-2 Level 4 ESD Protection

 We declare that the material of product compliance with RoHS requirements.

# **Applications**

- Cellular phones audio
- MP3 players
- Digital cameras
- Portable applicationss
- mobile telephone

### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Air Contact Contact discharge		±25 ±25	kV kV
ESD Voltage Per Human Body Model		16	kV
Total Power Dissipation on FR-5 Board (Note 1) @ T <sub>A</sub> =25 ℃	PD	150	Mw
Junction and Storage Temperature Range	TJ,TSTTh	-55 to 150	$^{\circ}$ C
Lead Solder Temperature – Maximum (10 Second Duration)	TL	260	$^{\circ}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Rating are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.1. FR-5 = 1.0\*0.75\*0.62 in.

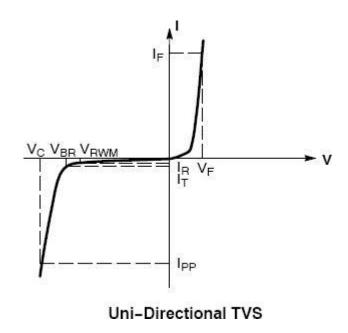
#### **Reference News**

PACKAGE OUTLINE	Circuit Diagram	Marking
		2C
DFN1006-2L		



# Electrical Parameters (TA = 25°C unless otherwise noted)

Symbol	Parameter		
<b>I</b> PP	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @ IPP		
VRWM	Working Peak Reverse Voltage		
lR	Maximum Reverse Leakage Current @ VRWM		
V <sub>BR</sub>	Breakdown Voltage @ I⊤		
lτ	Test Current		
lF	Forward Current		
VF	Forward voltage @ I <sub>F</sub>		
PPK	Peak Power Dissipation		
С	Max. Capacitanoe @V <sub>R</sub> = 0 and f =1 MHz		



## **ELECTRICAL CHARACTERISTICS**

(TA=25 ℃unless otherwise noted, VF=0.9V Max. @ IF=10Ma for all types)

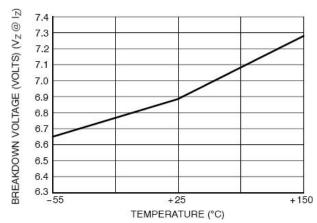
Device	V <sub>RWM</sub> (V)	l <sub>R</sub> ( µA) @	V <sub>BR</sub> (V) @ I <sub>T</sub> (Note 2)	lt (mA)	I <sub>PP</sub> (A) (Note 3)	Vc (V) @ Max I <sub>PP</sub> (Note 3)	P <sub>PK</sub> (W) (8*20 μs)	C (pF)
	Max	Max	Min		Max	Max	Тур	Тур
ESD9N12BA-MS	12	1.0	1.33	1.0	5.8	23.4	140	30

Other voltage available upon request.

- 3. Surge current waveform per Figure 3.



# **TYPICALCHARACTERISTICS**



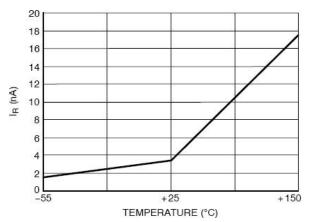


Figure 1. Typical Breakdown Voltage versus Temperature

Fig 2. Typical Leakage Current versus Temperature

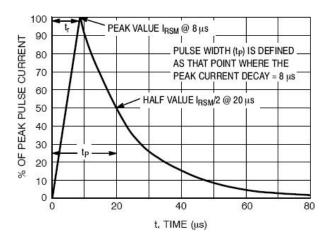


Figure 3. 8\*20 µs Pulse Waveform

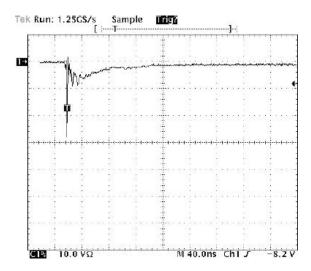
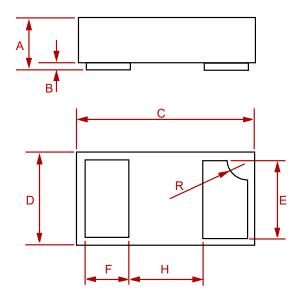


Fig 5. Negative 8kV contact per IEC 61000-4-2-

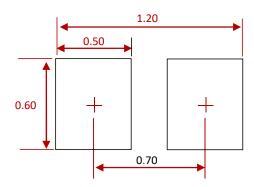


#### **PACKAGE MECHANICAL DATA**



Dim	Inches		Millimeters		
Dim	MIN	MAX	MIN	MAX	
А	0.0125	0.02	0.32	0.52	
В	0.000	0.002	0.00	0.05	
С	0.037	0.043	0.95	1.080	
D	0.022	0.027	0.55	0.680	
E	0.016	0.024	0.40	0.60	
F	0.008	0.012	0.20	0.30	
Н	0.015Typ.		0.40Тур.		
R	0.001	0.005	0.05	0.15	

# **Suggested Pad Layout**



#### NOTES:

- 1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
- THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY. CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
ESD9N12BA-MS	DFN1006-2L	10000



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